

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Daisaburo TAKASHIMA

SERIAL NO: NEW DIV. APPLICATION

GAU: UNASSIGNED

FILED: HEREWITH

EXAMINER: UNASSIGNED

FOR: SEMICONDUCTOR MEMORY DEVICE AND VARIOUS SYSTEMS MOUNTING THEM

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were provided in the prior application serial numbers 10/225,239, filed 8/22/02; 09/976,154, filed October 15, 2001; 09/609,058, filed June 30, 2000; 09/208,831, filed December 10, 1998 and 08/872,874, filed June 10, 1997 as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.

- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.

- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Eckhard H. Kuesters

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22850

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 244221US-2 SRD DIV		SERIAL NO. NEW DIV APPLICATION	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Daisaburo TAKASHIMA			
				FILING DATE HEREWITH		GROUP UNASSIGNED	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	5,345,415	09/06/94	Hironobu NAKAO, et al.			
	AB	5,303,182	04/12/94	Hironobu NAKAO, et al.			
	AC	5,956,655	9/1999	suzuki et al			
	AD	5,029,128	7-1991	TODA			
	AE	5,307,304	4/1994	SAITO ET AL			
	AF	5,373,463	12/1994	JONES, JR.			
	AG	5,383,150	1/1995	NAKAMURA ET AL			
	AH	5,517,445	5/1996	IMAI ET AL			
	AI	5,592,646	1/1997	THOMAS			
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO	07-176195	07/14/95	JAPAN (W/ ENGLISH ABSTRACT)			
	AP	95-1776	01/03/95	REPUBLIC OF KOREA			
	AQ	3-40298	2/1991	JAPAN			
	AR	6-140597	5/1994	JAPAN			
	AS						
	AT						
	AU						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AV	K. Takeuchi, et al., "Half-Vcc Plate Nonvolatile DRAMs with Ferroelectric Capacitors", Jeece Trans, Electron., Vol. E79-C, No. 2, Feb. 1996, pp. 234-242.					
	AW	K. Sunouchi, et al., "A surrounding Gate Transistor (SGT) Cell for 64/256Mbit DRAMs", IEDM, Dec. 1989, pp. 23-26.					
	AX	T. Hasegawa, et al., "An Experimental DRAM with a NAND-Structured Cell", IEEE International Solid-State Circuits Conference, Feb. 24, 1993, pp. 46-47.					
	AY	T. Sumi et al., "A 256kb Nonvolatile Ferroelectric Memory at 3V and 100ns", IEEE International Solid-State Circuits Conference, Feb. 18, 1994, pp. 268-269					
	AZ	H. Koike, et al., "A 60ns 1Mb Nonvolatile Ferroelectric Memory with Non-Driven Cell Plate Line Write/Read Scheme", IEEE International Solid-State Circuits Conference, Feb 10, 1996, pp. 368-369				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							